

FDC610PZ

P-Channel PowerTrench® MOSFET

-30V, -4.9A, 42mΩ

Features

- Max $r_{DS(on)}$ = 42mΩ at $V_{GS} = -10V$, $I_D = -4.9A$
- Max $r_{DS(on)}$ = 75mΩ at $V_{GS} = -4.5V$, $I_D = -3.7A$
- Low gate charge (17nC typical).
- High performance trench technology for extremely low $r_{DS(on)}$.
- SuperSOT™ -6 package: small footprint (72% smaller than standard SO-8) low profile (1mm thick).
- RoHS Compliant

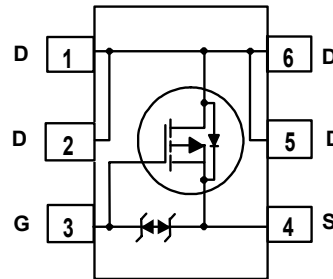
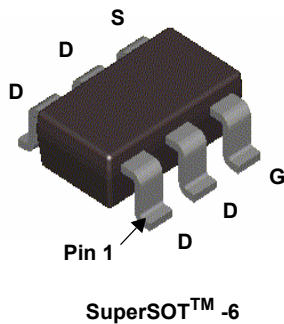


General Description

This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance. These devices are well suited for battery power applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Application

- DC - DC Conversion



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Rated | Units |
|----------------|--|-------------|-------|
| V_{DS} | Drain to Source Voltage | -30 | V |
| V_{GS} | Gate to Source Voltage | ±25 | V |
| I_D | Drain Current -Continuous (Note 1a) | -4.9 | A |
| | -Pulsed | -20 | |
| P_D | Power Dissipation (Note 1a) | 1.6 | W |
| | Power Dissipation (Note 1b) | 0.8 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

Thermal Characteristics

| | | | |
|-----------------|---|-----|------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 78 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1b) | 156 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|----------|---------|-----------|------------|-----------|
| .610Z | FDC610PZ | SSOT6 | 7" | 8mm | 3000units |

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|--|-----|-----|----------|----------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$ | -30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\mu\text{A}$, referenced to 25°C | | -22 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = -24\text{V}, V_{GS} = 0\text{V}$ | | | -1 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 25\text{V}, V_{DS} = 0\text{V}$ | | | ± 10 | μA |

On Characteristics

| | | | | | | |
|--|--|---|----|------|----|----------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = -250\mu\text{A}$ | -1 | -2.2 | -3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = -250\mu\text{A}$, referenced to 25°C | | 6 | | mV/ $^\circ\text{C}$ |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = -10\text{V}, I_D = -4.9\text{A}$ | | 36 | 42 | m Ω |
| | | $V_{GS} = -4.5\text{V}, I_D = -3.7\text{A}$ | | 58 | 75 | |
| | | $V_{GS} = -10\text{V}, I_D = -4.9\text{A}, T_J = 125^\circ\text{C}$ | | 50 | 60 | |
| g_{FS} | Forward Transconductance | $V_{DD} = -10\text{V}, I_D = -4.9\text{A}$ | | 15 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|---|-------------------|-----|------|----|
| C_{iss} | Input Capacitance | $V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ | | 755 | 1005 | pF |
| C_{oss} | Output Capacitance | | | 145 | 195 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 125 | 190 | pF |
| R_g | Gate Resistance | | $f = 1\text{MHz}$ | | 13 | |

Switching Characteristics

| | | | | | | | |
|--------------|-------------------------------|---|---------------------------------------|--|----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = -15\text{V}, I_D = -4.9\text{A}$ $V_{GS} = -10\text{V}, R_{GEN} = 6\Omega$ | | 7 | 14 | ns | |
| t_r | Rise Time | | | 4 | 10 | ns | |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 33 | 53 | ns | |
| t_f | Fall Time | | | 23 | 37 | ns | |
| Q_g | Total Gate Charge | | $V_{GS} = 0\text{V to } -10\text{V}$ | $V_{DD} = -15\text{V}, I_D = -4.9\text{A}$ | 17 | 24 | nC |
| Q_g | Total Gate Charge | | $V_{GS} = 0\text{V to } -4.5\text{V}$ | | 9 | 13 | nC |
| Q_{gs} | Gate to Source Gate Charge | | 2.9 | | | nC | |
| Q_{gd} | Gate to Drain "Miller" Charge | | 4.3 | | | nC | |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|---|---|--|------|------|----|
| I_S | Maximum Continuous Drain-Source Diode Forward Current | | | -1.3 | A | |
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{V}, I_S = -1.3\text{A}$ (Note 2) | | -0.8 | -1.2 | V |
| t_{rr} | Reverse Recovery Time | $I_F = -4.9\text{A}, di/dt = 100\text{A}/\mu\text{s}$ | | 19 | 35 | ns |
| Q_{rr} | Reverse Recovery Charge | | | 9 | 18 | nC |

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 78°C/W when mounted on a 1in^2 pad of 2 oz copper.



b. 156°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < $300\mu\text{s}$, Duty cycle < 2.0%.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

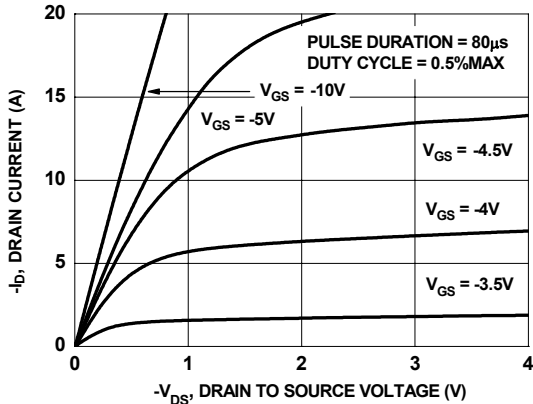


Figure 1. On-Region Characteristics

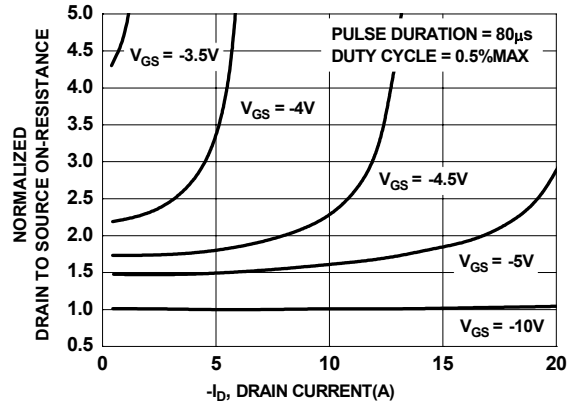


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

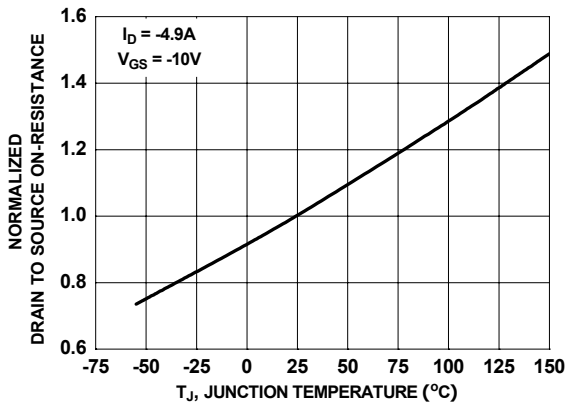


Figure 3. Normalized On-Resistance vs Junction Temperature

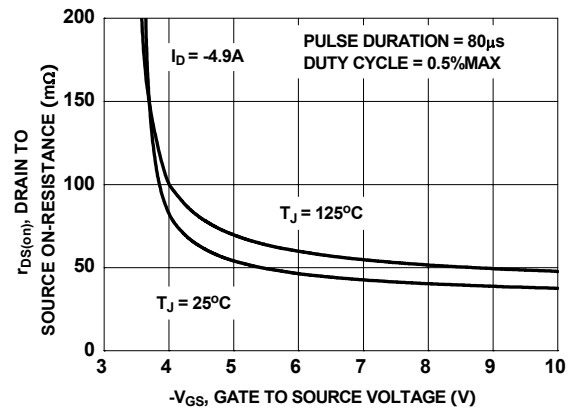


Figure 4. On-Resistance vs Gate to Source Voltage

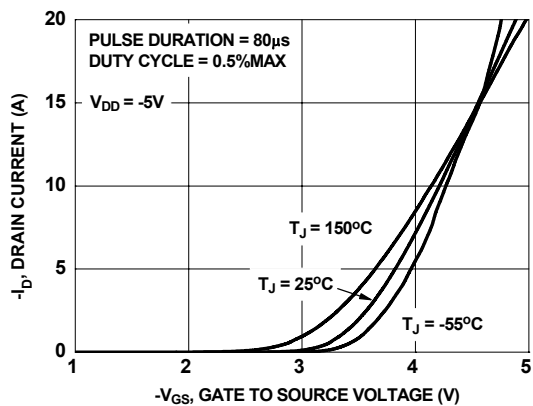


Figure 5. Transfer Characteristics

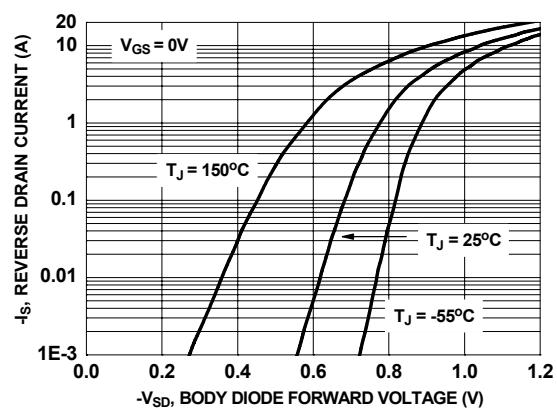


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

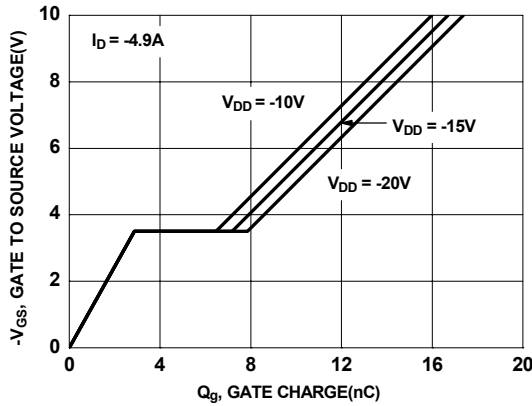


Figure 7. Gate Charge Characteristics

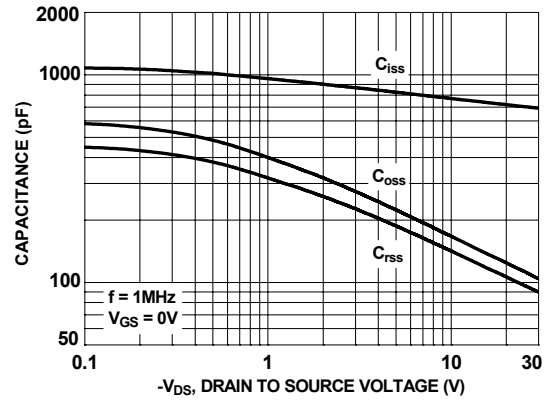


Figure 8. Capacitance vs Drain to Source Voltage

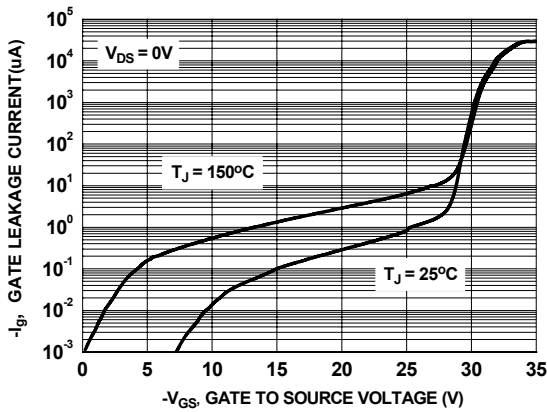


Figure 9. Gate Leakage Current vs Gate to Source Voltage

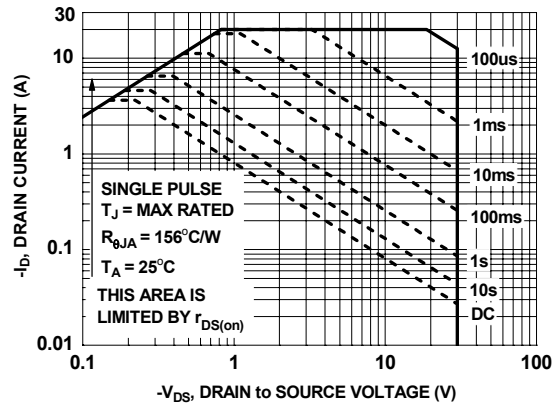


Figure 10. Forward Bias Safe Operating Area

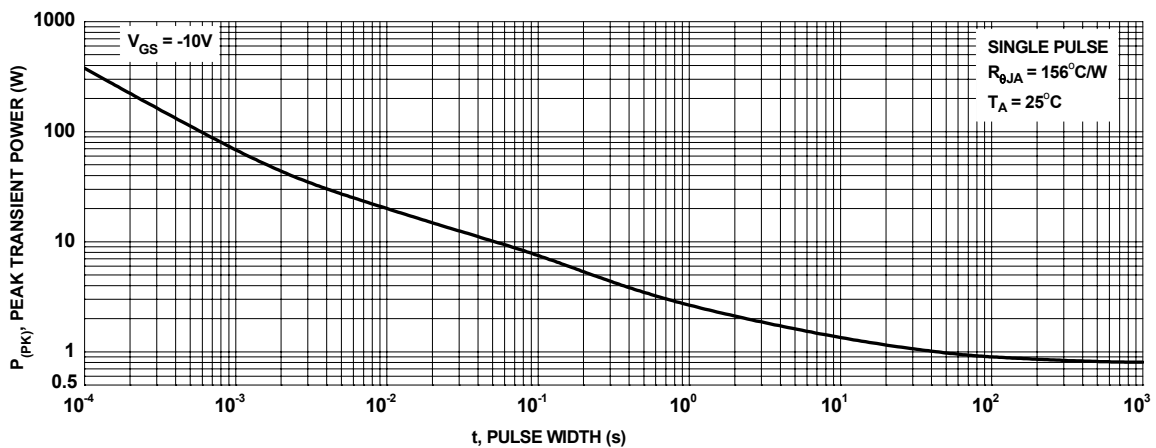


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

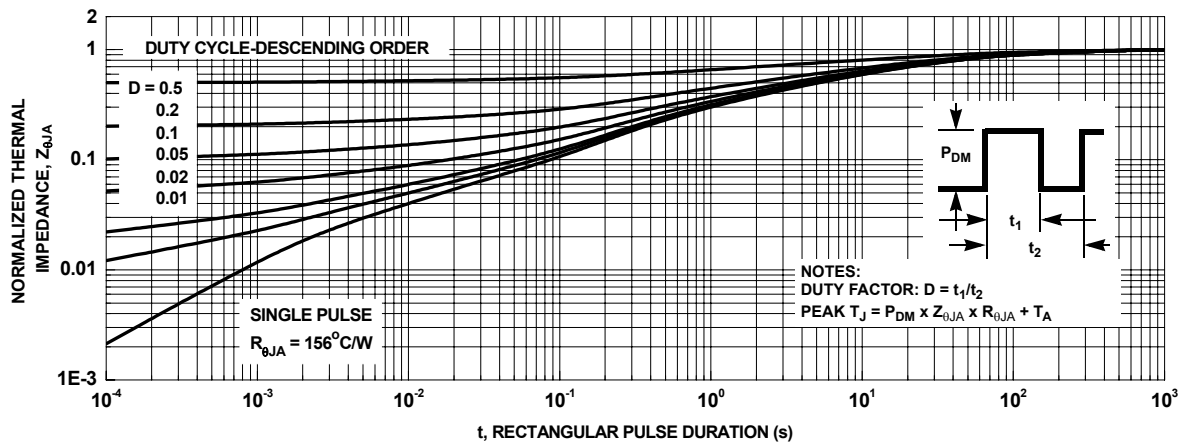


Figure 12. Transient Thermal Response Curve



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